Small Signal MOSFET 150 mAmps, 60 Volts

N-Channel TO-92

Features

• This is a Pb-Free Device*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain - Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage (R _{GS} = 1.0 MΩ)	V_{DGR}	60	Vdc
Gate–Source Voltage – Continuous – Non–repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I _D I _{DM}	150 1000	mAdc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

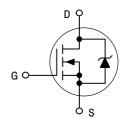


ON Semiconductor®

http://onsemi.com

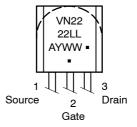
150 mA, 60 V $R_{DS(on)} = 7.5 \Omega$

N-Channel





MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

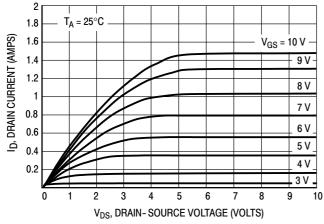
Characteris	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS		-	-	-	
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 100 µAdc)		V _{(BR)DSS}	60	-	Vdc
Zero Gate Voltage Drain Current $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125^{\circ}\text{C})$		I _{DSS}	- -	10 500	μAdc
Gate-Body Leakage Current, Forward (V _{GSF} = 30 Vdc, V _{DS} = 0)	I _{GSSF}	-	-100	nAdc	
ON CHARACTERISTICS (Note 1)			-	-	
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$		V _{GS(th)}	0.6	2.5	Vdc
Static Drain–Source On–Resistance $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Vdc}, T_C = 125^{\circ}\text{C})$		r _{DS(on)}	- -	7.5 13.5	Ω
Drain-Source On-Voltage ($V_{GS} = 5.0 \text{ Vdc}$, $I_D = 200 \text{ mAdc}$) ($V_{GS} = 10 \text{ Vdc}$, $I_D = 500 \text{ mAdc}$)		V _{DS(on)}		1.5 3.75	Vdc
On–State Drain Current $(V_{GS} = 10 \text{ Vdc}, V_{DS} \ge 2.0 \text{ V}_{DS(on)})$		I _{D(on)}	750	-	mA
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 500 mAdc)		9 _{fs}	100	-	μmhos
DYNAMIC CHARACTERISTICS		•			•
Input Capacitance		C _{iss}	-	60	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0,$ f = 1.0 MHz)	C _{oss}	-	25	
Reverse Transfer Capacitance	1 - 1.0 1.1.2,	C _{rss}	-	5.0	
SWITCHING CHARACTERISTICS (Note 1)					
Turn-On Delay Time	(V _{DD} = 15 Vdc, I _D = 600 mA,	t _{on}	-	10	ns
Turn-Off Delay Time	$R_{gen} = 25 \Omega, R_L = 23 \Omega$	t _{off}	-	10	

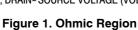
^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
VN2222LLG	TO-92 (Pb-Free)	1000 Unit / Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





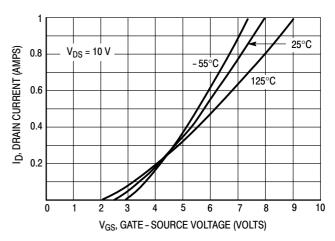


Figure 2. Transfer Characteristics

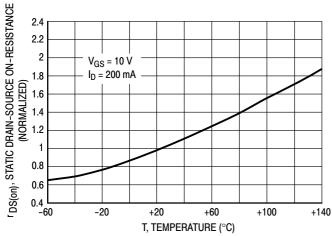


Figure 3. Temperature versus Static Drain-Source On-Resistance

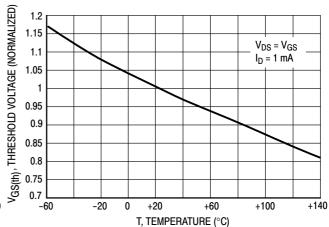
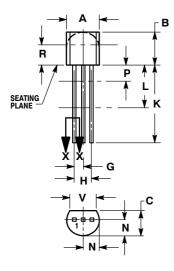


Figure 4. Temperature versus Gate Threshold Voltage

PACKAGE DIMENSIONS

TO-92 CASE 29-11 **ISSUE AM**



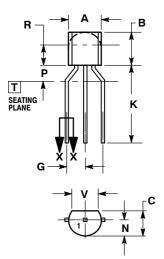
STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER 1. ASMF Y14 5M 1994
- CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
C	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 22: PIN 1. SOURCE 2. GATE 3.

DRAIN

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ite (SCILLC) . Solitude services are inject to make changes without further holice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative